DMG20102

Silicon NPN epitaxial planar type (Tr1) Silicon PNP epitaxial planar type (Tr2)

For general amplification

■ Features

- \bullet High forward current transfer ratio h_{FE} with excellent linearity
- ullet Low collector-emitter saturation voltage $V_{\text{CE(sat)}}$
- Halogen-free / RoHS compliant
 (EU RoHS / UL-94 V-0 / MSL: Level 1 compliant)

■ Marking Symbol: CY

■ Basic Part Number

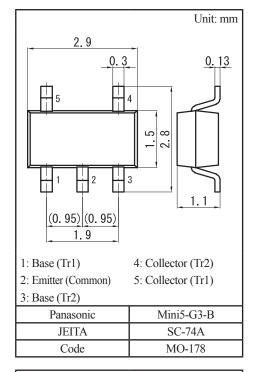
DSC2002 + DSA2002 (Common emitter)

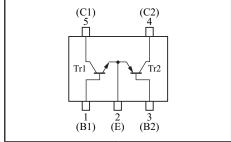
■ Packaging

DMG201020R Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25$ °C

	Parameter	Symbol	Rating	Unit
Tr1	Collector-base voltage (Emitter open)	V _{CBO}	60	V
	Collector-emitter voltage (Base open)	V _{CEO}	50	V
	Emitter-base voltage (Collector open)	V _{EBO}	5	V
	Collector current	I_{C}	500	mA
	Peak collector current	I_{CP}	1	A
Tr2	Collector-base voltage (Emitter open)	V _{CBO}	-60	V
	Collector-emitter voltage (Base open)	V _{CEO}	-50	V
	Emitter-base voltage (Collector open)	$V_{\rm EBO}$	-5	V
	Collector current	I_{C}	-500	mA
	Peak collector current	I_{CP}	-1	A
Overall	Total power dissipation	P_{T}	300	mW
	Junction temperature	T_{j}	150	°C
	Operating ambient temperature	T _{opr}	-40 to +85	°C
	Storage temperature	T _{stg}	-55 to +150	°C





■ Electrical Characteristics $T_a = 25$ °C±3°C

• Tr1

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = 10 \mu A, I_E = 0$	60			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = 2 \text{ mA}, I_{\rm B} = 0$	50			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 10 \mu A, I_C = 0$	5			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 20 \text{ V}, I_{E} = 0$			0.1	μΑ
Farment transfer artis	h _{FE1}	$V_{CE} = 10 \text{ V}, I_{C} = 150 \text{ mA}$	120		340	
Forward current transfer ratio	h _{FE2}	$V_{CE} = 10 \text{ V}, I_{C} = 500 \text{ mA}$	40			
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = 300 \text{ mA}, I_B = 30 \text{ mA}$		0.1	0.6	V
Transition frequency	f_T	$V_{CE} = 10 \text{ V}, I_{C} = 50 \text{ mA}$		160		MHz
Collector output capacitance (Common base, input open circuited)	C _{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		4.8	15	pF

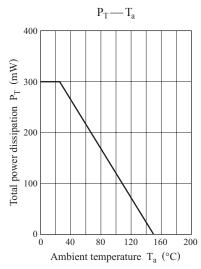
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

• Tr2

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = -10 \mu \text{A}, I_{\rm E} = 0$	-60			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-50			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -10 \mu\text{A}, I_C = 0$	-5			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{\rm CB} = -20 \text{ V}, I_{\rm E} = 0$			-0.1	μΑ
Forward current transfer ratio	h _{FE1}	$V_{CE} = -10 \text{ V}, I_{C} = -150 \text{ mA}$	120		340	
Forward current transfer fatto	h _{FE2}	$V_{CE} = -10 \text{ V}, I_{C} = -500 \text{ mA}$	40			
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = -300 \text{ mA}, I_B = -30 \text{ mA}$		-0.2	-0.6	V
Base-emitter saturation voltage	V _{BE(sat)}	$I_C = -300 \text{ mA}, I_B = -30 \text{ mA}$		- 0.9	-1.5	V
Transition frequency	f_T	$V_{CE} = -10 \text{ V}, I_{C} = -50 \text{ mA}$		130		MHz
Collector output capacitance (Common base, input open circuited)	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		7.3	15	pF

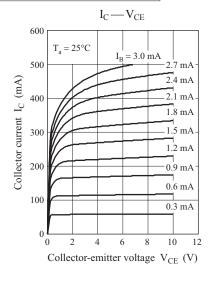
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

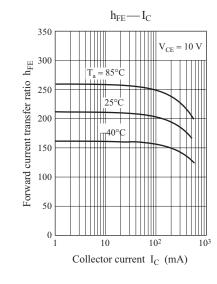
Common characteristics chart

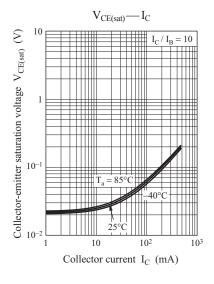


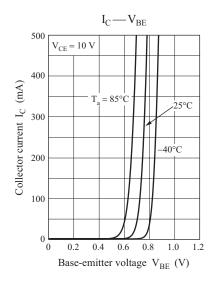
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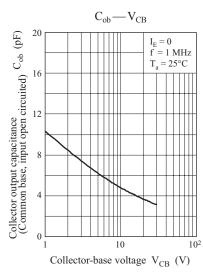
Characteristics charts of Tr1

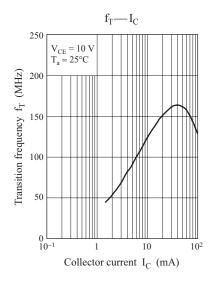




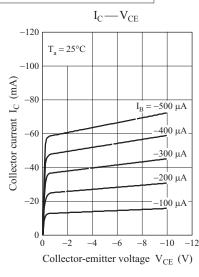


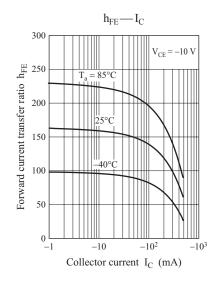


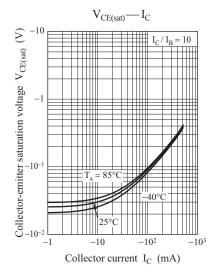




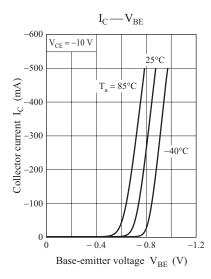
Characteristics charts of Tr2

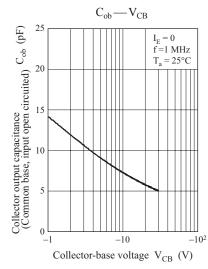


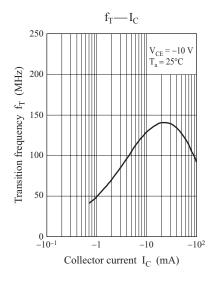




Ver. DED 3



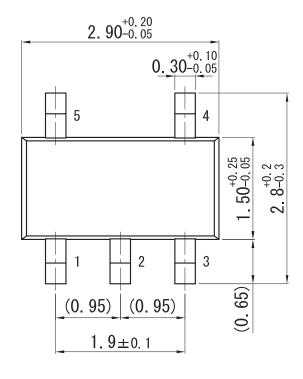


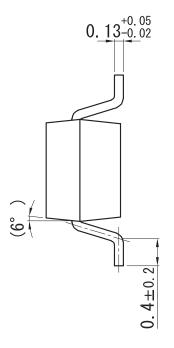


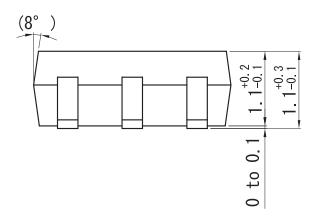
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Mini5-G3-B

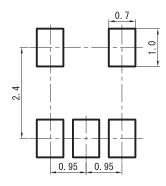
Unit: mm







■ Land Pattern (Reference) (Unit: mm)



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